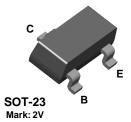


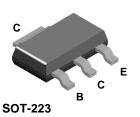
### MPSA64

### MMBTA64

#### PZTA64







## **PNP Darlington Transistor**

This device is designed for applications requiring extremely high current gain at currents to 800 mA. Sourced from Process 61.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current - Continuous	1.2	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

  3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

#### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic		Units		
		MPSA64	*MMBTA64	**PZTA64	
P <sub>D</sub>	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

<sup>\*\*</sup>Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min.  $6 \, \text{cm}^2$ .

#### **PNP Darlington Transistor**

(continued)

#### **Electrical Characteristics**

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units					
OFF CHAI	OFF CHARACTERISTICS									
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu\text{A},  I_B = 0$	30		V					
I <sub>CBO</sub>	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		100	nA					
I <sub>EBO</sub>	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		100	nA					

#### ON CHARACTERISTICS\*

h <sub>FE</sub>	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000 20,000		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$		1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$		2.0	V

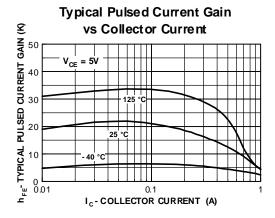
#### SMALL SIGNAL CHARACTERISTICS

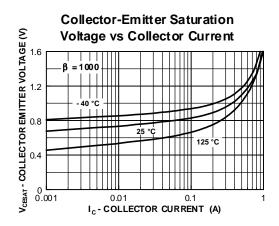
f⊤	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	125	MHz
		f = 100 MHz		

<sup>\*</sup>Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

**NOTE:** All voltages (V) and currents (A) are negative polarity for PNP transistors.

## **Typical Characteristics**



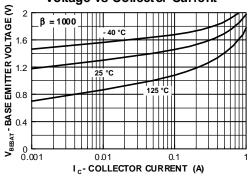


#### **PNP Darlington Transistor**

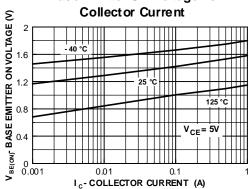
(continued)

#### Typical Characteristics (continued)

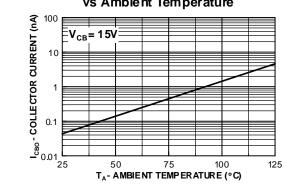
#### **Base-Emitter Saturation** Voltage vs Collector Current



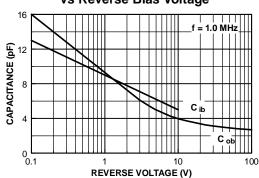
## Base Emitter ON Voltage vs



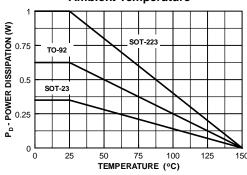
#### Collector-Cutoff Current vs Ambient Temperature

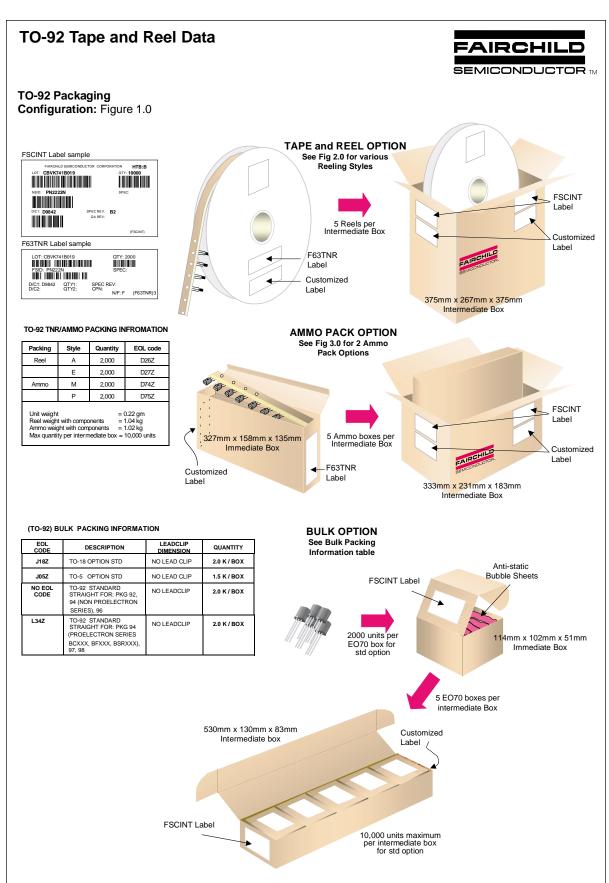


#### **Input and Output Capacitance** vs Reverse Bias Voltage



#### **Power Dissipation vs Ambient Temperature**



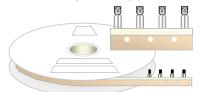


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#### TO-92 Tape and Reel Data, continued

#### **TO-92 Reeling Style** Configuration: Figure 2.0

#### Machine Option "A" (H)

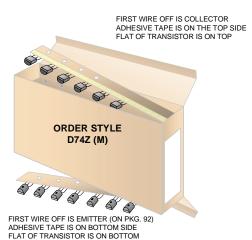


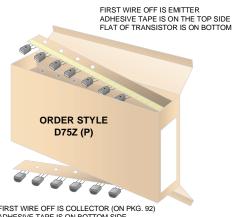
Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

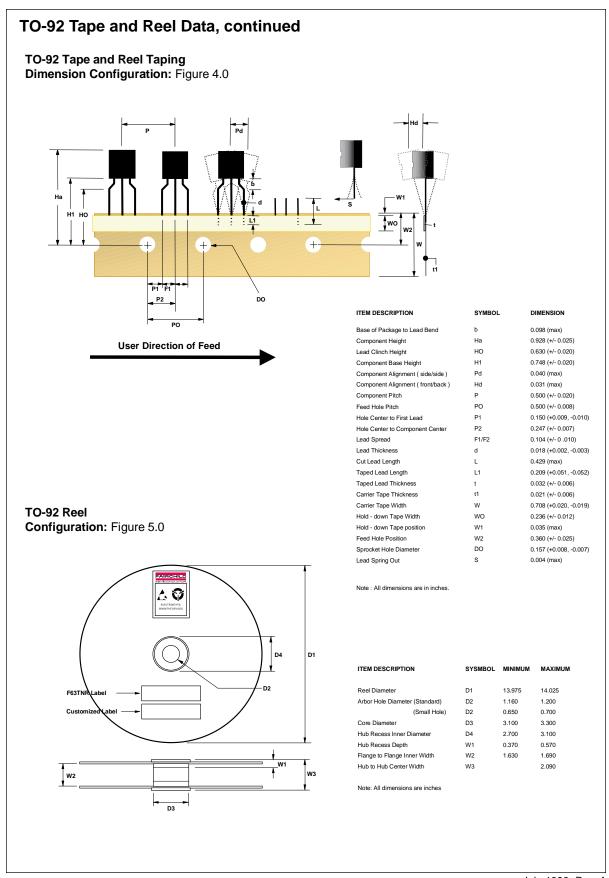
Style "E", D27Z, D71Z (s/h)

#### **TO-92 Radial Ammo Packaging** Configuration: Figure 3.0





FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

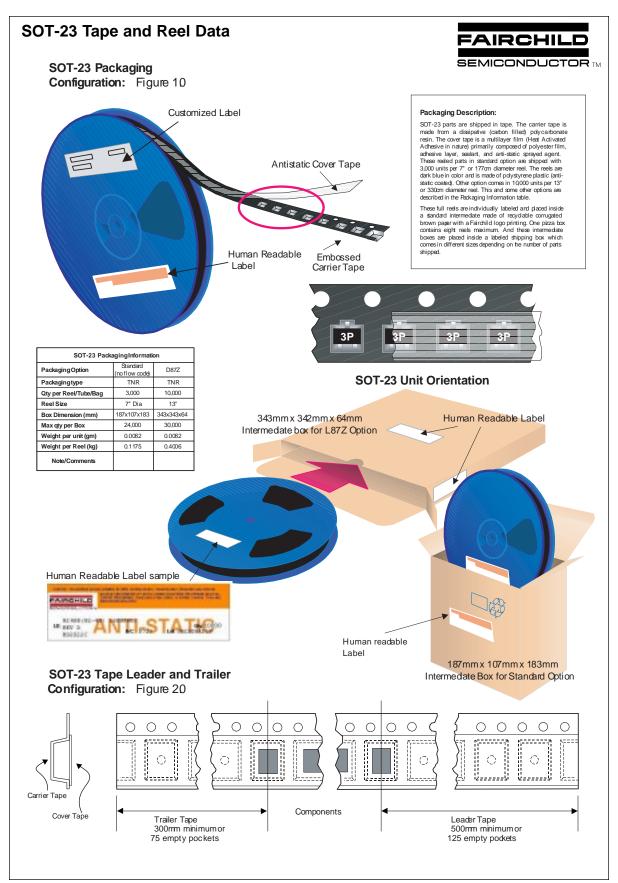


## **TO-92 Package Dimensions** FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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0.095 0.084 2.13

January 2000, Rev. B

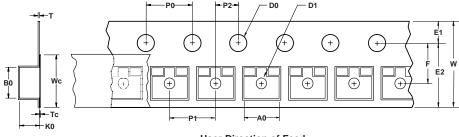


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#### SOT-23 Tape and Reel Data, continued

#### **SOT-23 Embossed Carrier Tape**

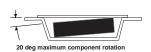
Configuration: Figure 3.0



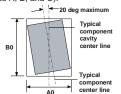
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



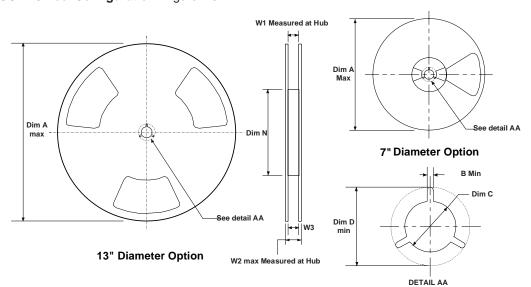
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

#### SOT-23 Reel Configuration: Figure 4.0

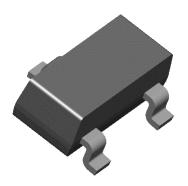


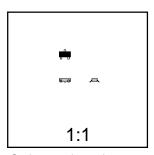
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

#### **SOT-23 Package Dimensions**



## SOT-23 (FS PKG Code 49)

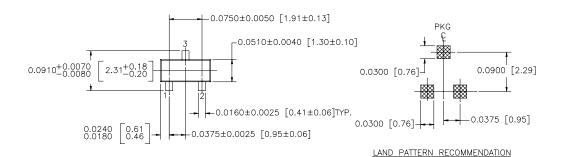


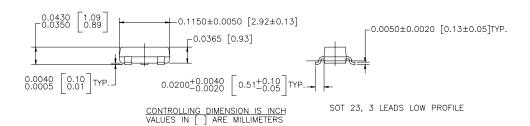


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082



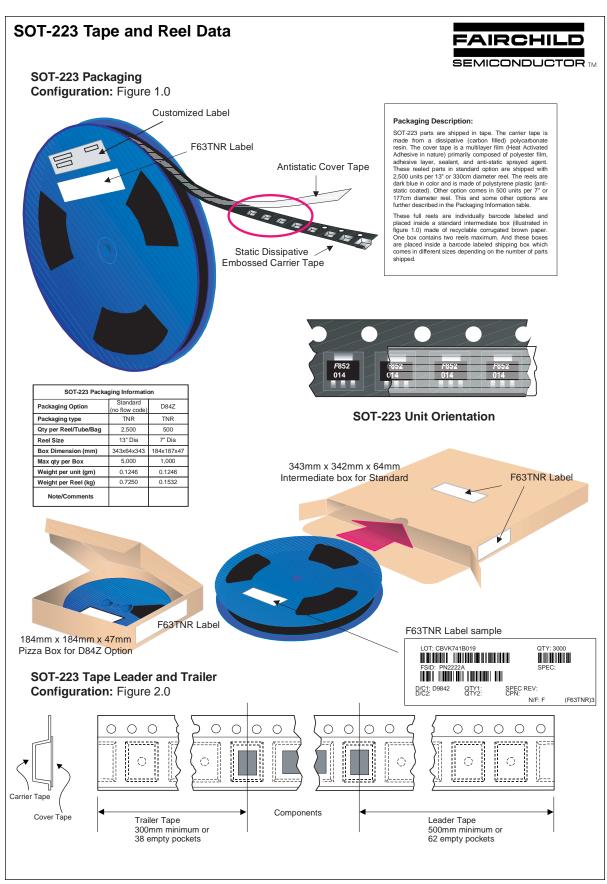


NOTE: UNLESS OTHERWISE SPECIFIED

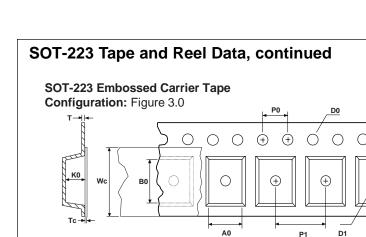
- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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September 1998, Rev. A1



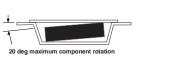
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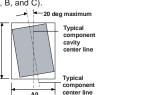
	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-223</b> (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

**User Direction of Feed** 

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



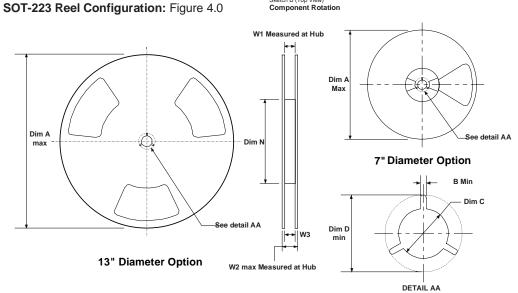
Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement



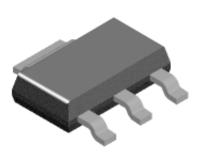
	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4	
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4	

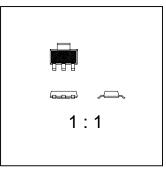
July 1999, Rev. B

#### **SOT-223 Package Dimensions**



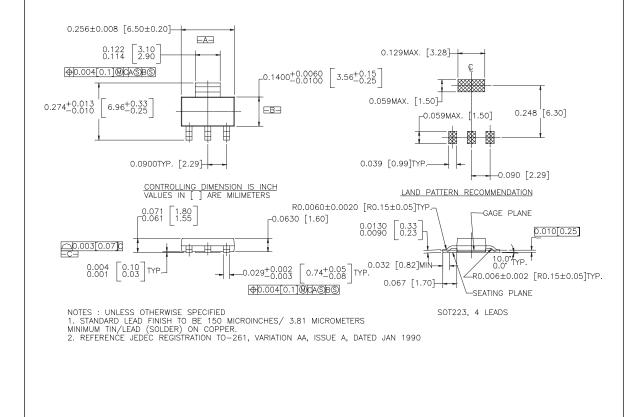
## SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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September 1999, Rev. C

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Rev. G